Calculated vibrational and electronic properties of various sodium thiogerm anate glasses

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A b stract. We study the vibrational and electronic properties of $(x)Na_2S-(1-x)GeS_2$ glasses through DFT-based molecular dynamics simulations, at di erent sodium concentrations (0 < x < 0.5). We compute the vibrational density of states for the di erent sam ples in order to determ ine the contribution of the Na⁺ ions in the VDOS.W ith an in-depth analysis of the eigenvectors we determ ine the spatial and atom ic localization of the di erent modes, and in particular in the zone corresponding to the Boson peak. We also calculate the electronic density of states as well as the partial EDOS, in order to determ ine the impact of the introduction of the sodium modil ers on the electronic properties of the GeS₂ matrix.

PACS num bers: 61.43 Fs,61.43 Bn,71 23 Cq,71 23.-k,71.15 Pd

1. Introduction

Sodium thiogermanate $(x)Na_2S-(1-x)GeS_2$ glasses are good solid electrolytes, with a high ionic conductivity at room temperature [1, 2]. As in other glassy systems, the ionic transport process has been clearly determined but its microscopic origin is still not well understood. In particular the mechanisms leading to the high conductivity at room temperature are not clearly established: is the conductivity dominated by random back and forth jumps [3] or do preferential pathways (\channels") exist inside the glassy matrix as in am orphous silica [4]? A rst step in the comprehension of these mechanisms is to determ ine the e ect of the modi er ions (N a) on the physical properties of the glass (GeS). To that purpose, theoretical studies, and in particular molecular dynamics (M D) simulations are interesting tools that provide detailed inform ations at the atom ic level on the modi cations of the am orphous sample as the concentration of sodium is increased. These modi cations have then to be connected to the evolution of the ionic transport if this connection exists.

In previous works we have studied germanium disul de glasses (GeS_2) through DFT-based MD simulations [5, 6, 7]. The results provided by our simulations were in very good agreement with the existing experimental data. Furtherm ore additional informations at the atom is scale provided by these simulations were found to explain some properties observed experimentally at the macroscopic scale especially concerning the vibrational and electronic properties of GeS_2 glasses.

In this paper we aim to analyze Na-Ge-S system s using the same model, in order to study the impact of the Na⁺ ions in GeS₂ glasses. Although similar studies have been performed in other glassy systems, such as SiO₂ [4], showing the evidence of conduction channels created dynamically by the Na cations inside the glass, no MD simulations have been performed yet in sodium thiogermanate glasses to our knowledge. The aim is in ne to analyze the in uence of the glassy matrix on the conduction properties: do the conduction channels exist also in chalcogenide glasses or are they specific to oxide glasses? A re the modil cations introduced by the alkali ions similar in both types of glasses? To that purpose, we focus here (in a rst step) on the vibrational and electronic properties of Na-Ge-S glasses, which should be directly connected to the ionic conduction properties. In order to evaluate the evolution of theses properties with the concentration of alkali ions, we simulate several (x)Na₂S-(1-x)GeS₂ samples, for 0 < x < 0.5, and analyze the vibrational and electronic densities of states for these different Na concentrations. The article is organized as follows : In section II we brie y describe the theoretical foundations of ourm odel, whereas in section III we study the vibrational properties of the am orphous sam ples through an in-depth analysis of the vibrational eigenvectors. Subsequently we study the electronic properties in section IV, and nally in section V we summarize the major conclusions of our work.

2.M odel

The code we have used is a rst-principles type molecular dynamics program called FIREBALL96, which is based on the local orbital electronic structure method developed by Sankey and Niklewski [8]. The foundations of this model are the Density Functional Theory (DFT) [9] within the Local Density Approximation (LDA) [10], and the non-local pseudopotential scheme [11]. The use of the non-self-consistent Harris functional [12], with a set of four atom ic orbitals (1s and 3p) per site that vanish outside a cut-o radius of $5a_0$ (2.645 A) considerably reduces the CPU time.

The pseudo-wave function of the system is given by the following equation:

$$j(\vec{k}; \boldsymbol{r}) = C^{J}(\vec{k}) \quad \text{fireball}(\boldsymbol{r}) \tag{1}$$

where j is the band index, $_{fireball}$ is the reball basis function for orbital, and $C^{j}(\mathcal{K})$ are the LCAO expansion coecients. Only the point is used to sample the Brillouin zone ($\mathcal{K} = 0$).

This model has given excellent results in many di erent chalcogenide systems over the last ten years [5, 13, 14]. In the present work we melt a crystalline -GeS2 con guration containing 258 particles at 2000K during 60 ps (24000 tim esteps) in a cubic box of 1921 A, until we obtain an equilibrated liquid. Subsequently we replace random by GeS_4 tetrahedral units by articial Na₂S₃ \m olecules", following a procedure similar to the one used in SiO 2 glasses [4], in order to obtain a given sodium concentration (the total num ber of atom s, N, is kept constant at 258). We generate thus eight (x)N $a_2S-(1-x)GeS_2$ samples at di erent sodium concentrations (x=0, 0.015, 0.03, 0.06, 0.11, 0.2, 0.33 and 0.5). The bounding box is rescaled each time so that the density matches its experimental counterpart (from 1921 A for x=0[15] to 18.3 A for x=0.5[16], in order to limit articial pressure e ects on the system. Then, we melt the resulting system at 2000K during 60 ps so that the system completely loses the memory of the initialarti cial con guration, and becomes a hom ogeneous liquid (x)N $aS - (1-x)G eS_2$ system. Finally, we quench the liquid structure at a quenching rate of 6.8 10^{14} K/s, decreasing the temperature to 300K through the glass transition temperature T_{g} , and we let our sample relax at 300K during 100 ps. The dynam icalm atrix and the electronic density of states have been calculated at the end of this relaxation time. It is worth noticing that the results obtained with FIREBALL96 on severalNa-Ge-S test samples are alm ost identical to those obtained with the self-consistent ab initio SIE STA code [17] in which the largest available basis set has been used. This shows the ability of our model to accurately describe sodium thiogerm anate glasses at a relatively reduced CPU time cost.

3. Results

3.1. Vibrational properties

First we compute the V ibrational Density of States (VDOS), which can be measured experimentally by inelastic neutron di raction spectroscopy. The VDOS is calculated through the diagonalization of D, the dynam ical matrix of the system given by:

D
$$(_{i};_{j}) = \frac{e^{2}E(_{i};_{j})}{e_{i}e_{j}}; = x;y;z$$
 (2)

for two particles i and j. Fig.1 presents the calculated VDOS for di erent values of x (for clarity only the results for x=0, x=0.2 and x=0.5 are shown). The VDOS of GeS₂ (x=0) has been studied in detail in a previous work [6] in which we have determ ined the presence of two bands (the acoustic and optic band), separated by a "gap", which was found to contain a few localized modes caused by bond defects. We can see in Fig. 1 how the introduction of sodium atom sm odi es the VDOS, and it appears clearly that the vibrational contribution of the N a atom s takes place between the acoustic and optic band (200 cm⁻¹). In the Na₂GeS₃ compound (x=0.5) the two bands cannot be distinguished anymore, since the density of states is almost at over the whole spectrum. It can also be seen that the introduction of sodium cations dim inishes the acoustic band especially on the low frequency side, contrarily to the optic band that rem ainspractically unchanged. The dim inution of the low frequency modes is counterbalanced by an accumulation of modes in the \gap" zone between 200 cm⁻¹ and 300 cm⁻¹ when the sodium concentration increases. The low-frequency zone at 35 cm⁻¹ has been attributed experimentally to the well-known \B oson peak", which is a signature of am orphous materials in the VDOS [18]. It appears in our simulation that above x= 0.2, the density of states in that zone decreases signi cantly (together with the rest of the acoustic band). Unfortunately, the VDOS of sodium thiogerm anate glasses has never been

m easured experim entally to our know ledge, and therefore we cannot con m this lack of low frequency m odes by experim ental data.

In order to measure the localization of the vibrational modes, we calculate the participation ratio P_r [19]:

$$P_{r} = \frac{\left(\frac{N}{i=1} \dot{\mathbf{j}} \dot{\mathbf{j}}_{i}(!) \dot{\mathbf{j}}^{2}\right)^{2}}{N \frac{N}{i=1} \dot{\mathbf{j}}_{i}(!) \dot{\mathbf{j}}^{4}}$$
(3)

where the sum mation is done over the N particles of the sample. If the mode corresponding to eigenvalue ! is delocalized and all atoms vibrate with equal amplitudes, then $P_r(!)$ will be close to 1. On the contrary, if the mode is strongly localized, then $P_r(!)$ will be close to 0. The results are shown in Fig 2, and it can be seen that the modes that appear in the zone between 200 cm⁻¹ and 300 cm⁻¹ in the sodium -enriched samples are relatively delocalized. The P_r , which is close to zero for GeS_2 in that region, become shigher as the N a concentration increases. An in-depth study of the vibrational eigenvectors in that region shows that these modes are mainly caused by sodium atoms, as it could be deduced from the VDOS (Fig.1). Although a few localized modes appear at the end of the optic band (beyond 480 cm⁻¹), it can be said that the contribution of the N a atom s in the VDOS is principally sensitive in delocalized modes (for x= 0.5, the maximum of Pr appears at 190 cm⁻¹). It should also be noted that in the region attributed to the B oson P eak (35 cm⁻¹) [20], the participation ratio is low er for sodium -enriched system s. Since we have previously seen that this zone show ed a lack of modes for x= 0.33 and x= 0.5 in comparison to the low values of x one can conclude that the remaining "soft modes" become e more localized when the N a concentration increases.

In order to calculate the spatial localization of the vibrational modes, we calculate the center of gravity r_g (!) of each mode of eigenvalue !, and the corresponding \localization" length L [21], as

$$\mathbf{r}_{g}(!) = \frac{\prod_{i=1}^{N} \mathbf{r}_{i} \mathbf{j} \mathbf{\hat{e}}_{i}(!) \mathbf{j}^{2} = m_{i}}{\prod_{i=1}^{N} \mathbf{j} \mathbf{\hat{e}}_{i}(!) \mathbf{j}^{2} = m_{i}}$$
(4)

and

$$L(!) = \frac{\sum_{i=1}^{N} j \dot{r}_{i} \qquad r_{g}(!) f \dot{f}_{i} = n_{i}}{\sum_{i=1}^{N} j \dot{r}_{i}(!) f = n_{i}}$$
(5)

where r_1 and m_1 are respectively the position and the atom ic mass of particle i. Periodic boundary conditions must be taken into account in these calculations. The localization length (Fig.3) represents the spatial localization of a given mode, and its maximal value corresponds to the half-size of the box. Beyond this length, the amplitude of the atom ic vibrations decreases signing cantly. It can be seen in Fig.3 that contrarily to the participation ratio, the localization length remains unchanged at low frequencies as the N a concentration increases, and corresponds approximately to the half-size of the box. The low frequency modes appear therefore completely delocalized in space, but the number of particles involved in these vibrations decreases as the sodium concentration becomes higher as shown by the decreasing participation ratio. This means that in pure GeS₂ a large amount of connected particles were involved in the low frequency modes whereas in Na-Ge-S glasses, Na breaks these connections and therefore small groups of particles (sm all participation ratio) scattered in the whole simulation box (large localization length) participate in these modes with the consequence of a decrease of the density of states at low frequency.

3.2. Electronic properties

S

The Sankey-N iklew skitschem e that has been described in section II allows the determ ination of the electronic energy eigenvalues for the dimentisamples. The Electronic Density of States (EDOS), which can be calculated by \binning" these eigenvalues, has been measured experimentally by X-ray Photoelectron Spectroscopy (XPS) in GeS₂ and Na₂GeS₃ (x=0.5) systems [22]. In a previous work we have compared in GeS₂ our calculated EDOS with its experimental counterpart, and we have analyzed in detail the dimentificatures of the valence spectrum [7]. Three bands, called A, B and C were clearly distinguished, with good agreement with the XPS spectrum . We show in Fig.4 the valence band of our calculated EDOS for x=0 and x=0.5, whereas Fig.5 presents the calculated and experimental valence spectra of Na₂GeS₃. We can see in Fig.4, that the impact of the sodium atom s in the EDOS of am orphous GeS₂ is negligible (the spectra of the other simulated samples are rather similar to these two graphs). It can however be seen that the width of band B decreases with the introduction of the sodium atom s in the glassy sample and that the density of states in band C increases. In addition, the small peak at the end of band A is slightly shifted in the sodium -enriched sample. We can see in Fig.5 that this calculated spectrum is

in good agreem ent with the experim ental data, even though a sm all energy shift is visible at the end of band C (1 eV).

In order to determ ine which atom ic orbitals are responsible of these bands, we must compute the partial EDOS by sum ming the $f_{C}^{j}(K)f_{j}$ for each element and each orbital. Here the s and p orbitals of germ anium and sulfur atom s can be distinguished, as well as the s orbitals of sodium atom s. We have scaled the partialEDOS so that that their sum is equal to the totalEDOS. The results are illustrated in Fig.6, where the solid line represents the totalEDOS and the dashed area shows the contribution of a given orbital.

It can be seen that zone A is almost exclusively caused by the 3s orbitals of sulfur atoms. The small peak at the end of this band, which appears to be shifted for x=0.5, has been attributed in GeS₂ to S-S hom opolar bonds[7]. We distance that in the Na₂GeS₃ sample these hom opolar bonds are also connected to a sodium atom, which changes thus the energy eigenvalues of these orbitals. This explains why the modes at the end of band A have a higher energy (0.3 eV) for x=0.5 than in the GeS₂ compound. The band B, which is sharper for sodium -enriched systems (Fig.4), is mainly caused by the 4s orbitals of Ge atoms (here the respective concentrations of each element must be taken into account). This property has been observed experimentally, and has been attributed to the increase of the Ge-Ge interatom ic length, limiting thus the height of band B [22]. We have analyzed the interatom ic distances for Ge-Ge pairs, and we can con im this experimental prediction. Indeed, the distance between germanium pairs increases in both edge-sharing and corner-sharing units. In GeS₂ these lengths were found to be equal respectively to 2.91 A and 3.41 A [5], whereas in the Na₂GeS₃ sam ple they become equal to 3.01 A and 3.67 A. Therefore this variation could indeed be responsible of the evolution of band B when the sodium concentration increases.

We see that the contribution of the sodium atom s in the EDOS appears at the beginning of band C. The electronic energy of the 3s orbitals of sodium atom s is therefore close to the energy of the 4p orbitals of germ anium atom s, and both are responsible of the shoulder which can be distinguished at the beginning of this band. It can be seen at the end of band C that the last occupied states before the Ferm i Level are caused by the 3p orbitals of sulfur atom s as in GeS_2 , and no contribution of the Na ions could be determ ined at the top of the valence band.

The localization of the electronic eigenstates can be evaluated through the inverse participation ratio ($\mathbb{P}R$), which can be calculated with the M ulliken charges [23]. It appears that in comparison to the $\mathbb{P}R$ of GeS_2 , which has been shown in our previous work [7], no localized states concerning sodium atom shave been found. Indeed the $\mathbb{P}R$ of Na_2GeS_3 is very similar to that of GeS_2 and therefore it is not shown here.

4. Conclusion

We have studied the vibrational and electronic properties of sodium thiogerm anate glasses through DFT – based m olecular dynam ics simulations for dierent sodium concentrations. We nd that the vibrational contribution of the sodium ions in the VDOS takes place between the acoustic and optic band. Thus, the modes in that zone are almost exclusively caused by the Na particles of the system, and are due to delocalized motions of the ions. In the same time, the acoustic band decreases, and in particular the well known \soft modes" tend to disappear because of the introduction of the sodium atoms in the system, which limits the collective vibrations connected to the Boson peak in that zone. This exclusions of Na in (x)Na₂S-(1-x)GeS₂ glasses is quite negligible. However, several variations could be seen in the three main contributions of the valence spectrum, and in particular in band B, which become es sharper in the sodium -enriched system s. This change can be attributed to the increase of the GeGe interatom ic length, as it has been proposed experimentally. With the calculation of the partial EDOS we nd that the polbitals of the germanium atom s, and no localized states could be attributed to the sodium ions at the top of the valence band.

This work is the st step in the study of the in uence of the alkali ions on the properties of GeS glasses and has to be continued by the analysis of the structural changes before trying to link all these modi cations to the transport properties: this work is currently in progress.

A cknow ledgm ents Parts of the simulations have been performed on the computers of the \Centre Inform atique National de l'Enseignem ent Superieur" (CINES) in Montpellier.

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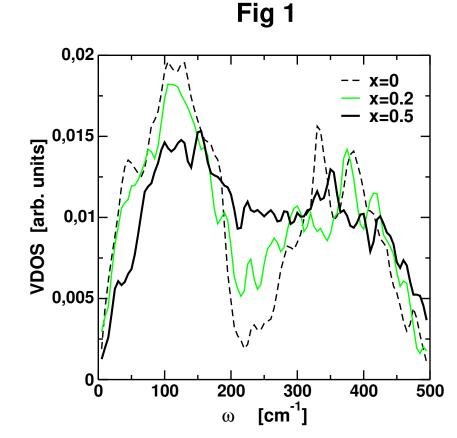


Figure 1. Calculated VDOS of (x)Na₂S-(1-x)GeS₂ for x= 0, x= 0.2 and x= 0.5.

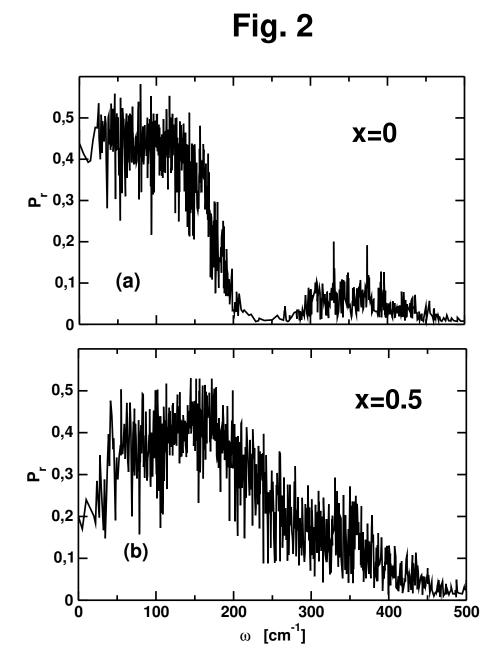


Figure 2. Participation ratio (see text for de nition) of (a) GeS_2 (x=0), and (b) Na_2GeS_3 (x=0.5), as a function of !.

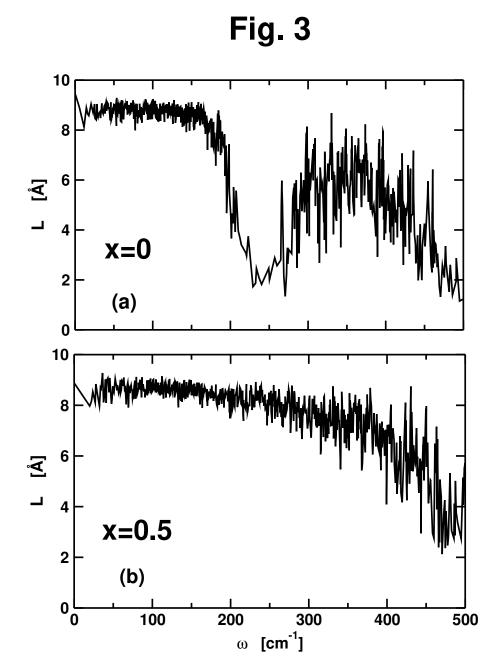


Figure 3. Localization length (see text for de nition) of GeS₂ (x=0) (a), and Na₂GeS₃ (x=0.5) (b), as a function of !.

Fig. 4

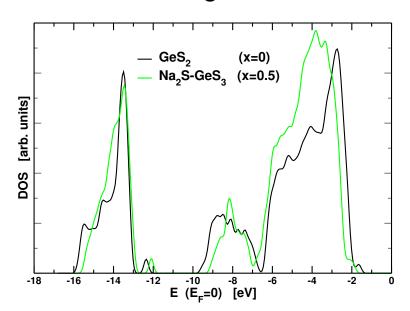
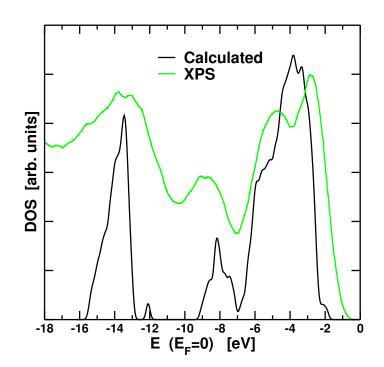


Figure 4. Calculated EDOS of GeS $_2$ and N $a_2 G\, eS_3$ (a).





F igure 5. Calculated EDOS of $N\,a_2\,G\,eS_3\,$ (a) and experimental valence spectrum obtained by XPS m easurements (Ref.18) .



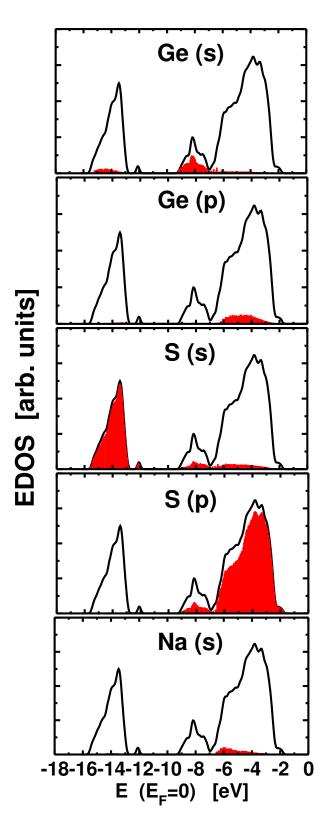


Figure 6. PartialEDOS of N $a_2 G \, eS_3$ (shaded area) and totalEDOS (solid line).